

GaAs IC SP2T Non-Reflective Switch With Driver 20 MHz–2 GHz



AE002M2-29, AE002M2-53

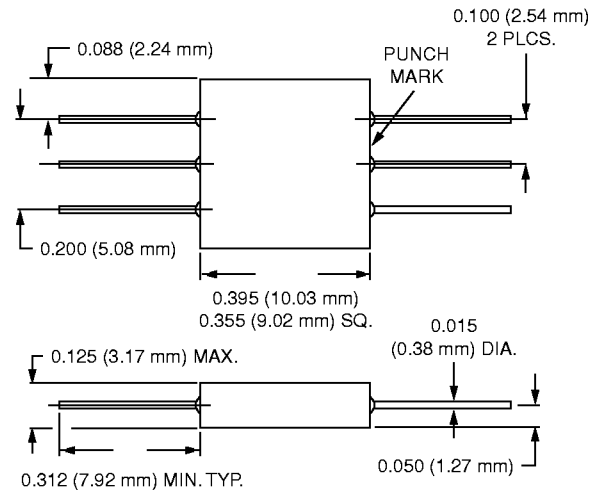
Features

- Single 5 V Supply Voltage
- Non-Reflective All Ports
- Single Line Control
- Capable of Meeting MIL-STD Requirements⁴

Description

The AE002M2-29 is a SP2T non-reflective FET MMIC switch. This switch consists of a GaAs SP2T chip and a silicon CMOS driver. It operates with 5 V bias and a single logic control. This unit is used in military switched filter banks, instruments and telecommunication applications. The AE002M2-53 is the gullwing version for surface mount applications.

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Electrical Specifications at 25°C

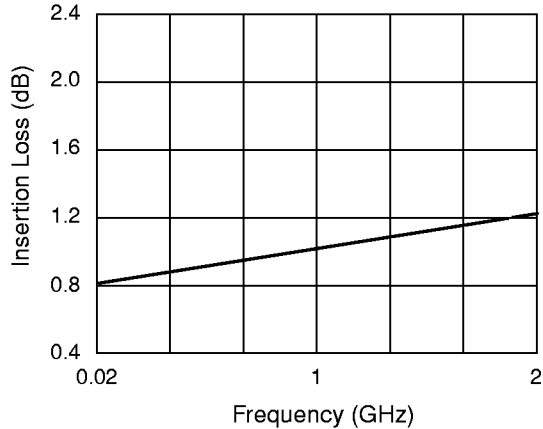
Parameter ¹	Frequency	Min.	Typ.	Max.	Unit
Insertion Loss ²	0.02–0.5 GHz		0.8	0.9	dB
	0.50–1.0 GHz		1.0	1.2	dB
	1.00–2.0 GHz		1.2	1.4	dB
Isolation	0.02–0.5 GHz	55	58		dB
	0.50–1.0 GHz	50	52		dB
	1.00–2.0 GHz	45	48		dB
VSWR (I/O)	0.02–0.5 GHz		1.2:1	1.3:1	
	0.50–1.0 GHz		1.4:1	1.5:1	
	1.00–2.0 GHz		1.6:1	1.7:1	

Operating Characteristics at 25°C

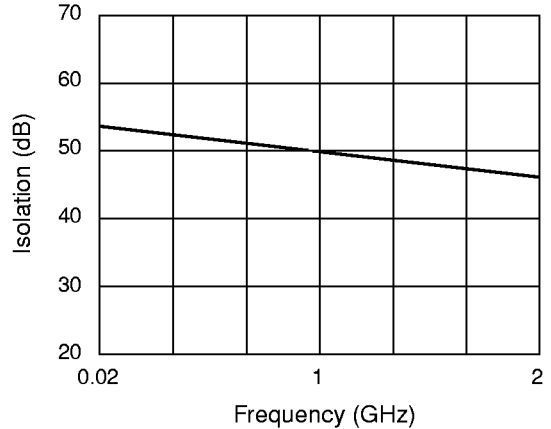
Parameter	Condition	Frequency	Min.	Typ.	Max.	Unit
Switching Characteristics	Rise, Fall (10/90% or 90/10% RF)			15		ns
	On, Off (50% CTL to 90/10% RF)			50		ns
	Video Feedthru ³			30		mV
Input Power for 1 dB Compression	5 V (7 V)	0.5–2 GHz		24 (28)		dBm
		0.001 GHz		16 (20)		dBm
Intermodulation Intercept Point (IP3)	For Two-tone Input Power 13 dBm	0.5–2 GHz		40		dBm
		0.02 GHz		29		dBm
Control Voltages	V_{Low}		0		0.8	V
	V_{High}		2.0		5.5	V
Supply Voltages	5 V @ 50 μ A Typ. 7 V @ 100 μ A Typ.					

1. All measurements made in a 50 Ω system, unless otherwise specified.
2. Insertion loss changes by 0.003 dB/°C.
3. Video feedthru measured with 1 ns risetime pulse and 500 MHz bandwidth.
4. See Quality/Reliability section.

Typical Performance Data



Insertion Loss vs. Frequency



Isolation vs. Frequency

Truth Table

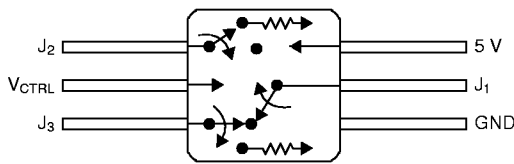
Control Logic	Condition J ₁ to	
	J ₂	J ₃
V _{CTRL} = 1	Insertion Loss	Isolation
V _{CTRL} = 0	Isolation	Insertion Loss

Absolute Maximum Ratings

Characteristic	Value
RF Input Power (RF In)	2 W > 500 MHz 0/7 V 0.5 W @ 50 MHz 0/7 V
Bias Voltage (V _B)	7.0 V
Control Voltage (V _C)	≤ 7.0 V
Operating Temperature (T _{OP})	-55°C to +125°C
Storage Temperature (T _{ST})	-65°C to +150°C
Thermal Resistance (Θ _{JC})	25°C/W

Do not allow control voltage to exceed bias voltage.

Pin Out



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